

# **Notice of References Cited**

Application/Control No.

09/928,356

Applicant(s)/Patent Under Reexam

Lempkowski et al.

Examiner

B. William Baumeister

Art Unit

2815

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## **U.S. PATENT DOCUMENTS**

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## **NON-PATENT DOCUMENTS**

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Eisenbeiser et al., Field effect transistors with SrTiOs gate dielectric on Si," 6 March 2000, Applied Physics Letters, Vol. 76, No. 10, pp.1324-1326.
V	Weiss, "Speed demon gets hooked on silicon," Science News Online, 9/15/2001.
W	"Motorola develops new super-fast chip," USA Today, 9/4/2001.
X	Valigra, "Motorola Lays GaAs on Si Wafer," AsiaBiz Tech, Nov. 2001.

\* A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).

<sup>1</sup> Dates in MM-YYYY format are publication dates.

<sup>2</sup> Classifications may be U.S. or foreign.

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U	"Holy Grail! Motorola claims high-yield GaAs breakthrough," Micromagazine.com (no date available).
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W	
X	

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